



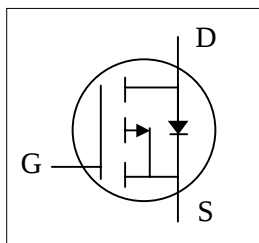
**Advanced Power
Electronics Corp.**

AP9435GG

Pb Free Plating Product

*P-CHANNEL ENHANCEMENT MODE
POWER MOSFET*

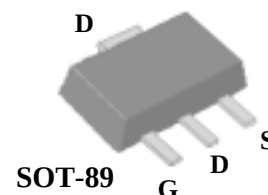
- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Single Drive Requirement
- ▼ RoHS Compliant



BV_{DSS}	-30V
$R_{DS(ON)}$	50m Ω
I_D	- 4.2A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^3$	- 4.2	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^3$	-3.4	A
I_{DM}	Pulsed Drain Current ¹	-20	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation	1.25	W
	Linear Derating Factor	0.01	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal Resistance Junction-ambient ³ Max.	100	$^\circ\text{C}/\text{W}$



AP9435GG

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =-1mA	-	-0.1	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-4A	-	-	50	mΩ
		V _{GS} =-4.5V, I _D =-2A	-	-	90	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance ²	V _{DS} =-10V, I _D =-4A	-	6	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =-24V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-4A	-	10	16	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-25V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	6	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	10	-	ns
t _r	Rise Time	I _D =-1A	-	7	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-10V	-	26	-	ns
t _f	Fall Time	R _D =15Ω	-	14	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	520	830	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	180	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	130	-	pF
R _g	Gate Resistance	f=1.0MHz	-	16	24	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time	I _S =-4A, V _{GS} =0V,	-	30	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	24	-	nC

Notes:

- 1.Pulse width limited by safe operating area.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mount on FR4 board, t ≤ 10s.

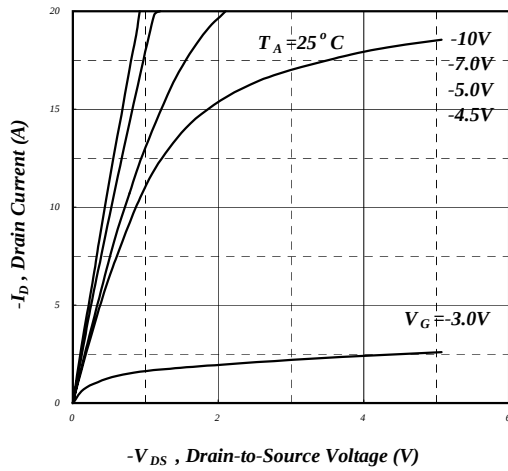


Fig 1. Typical Output Characteristics

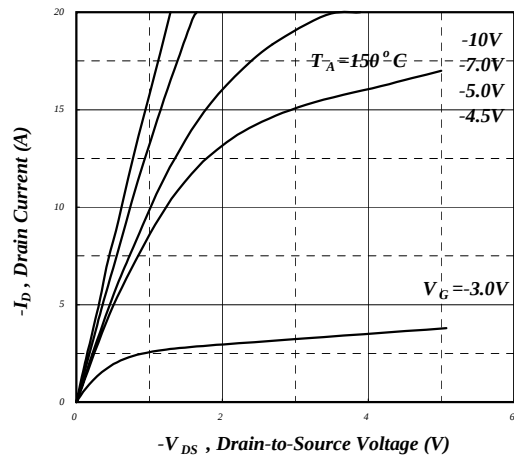


Fig 2. Typical Output Characteristics

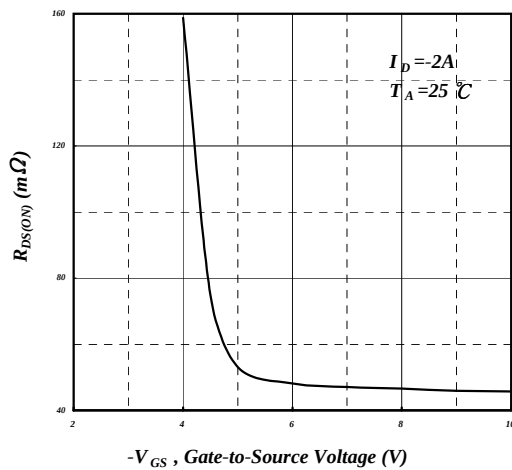


Fig 3. On-Resistance v.s. Gate Voltage

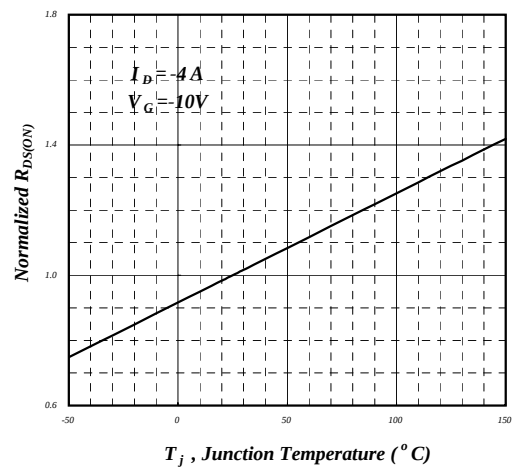


Fig 4. Normalized On-Resistance v.s. Junction Temperature

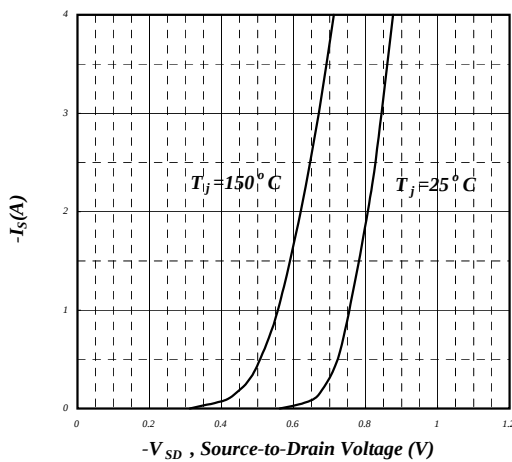


Fig5. Forward Characteristic of Reverse Diode

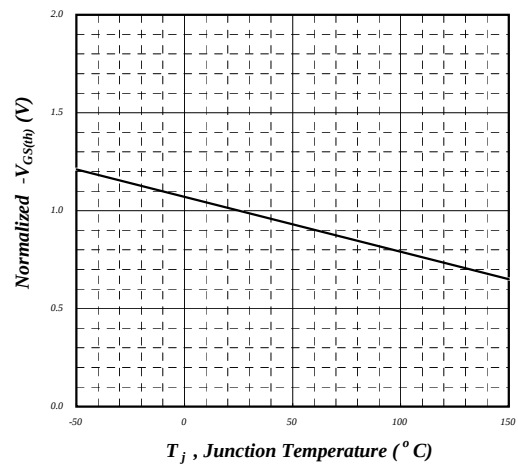


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

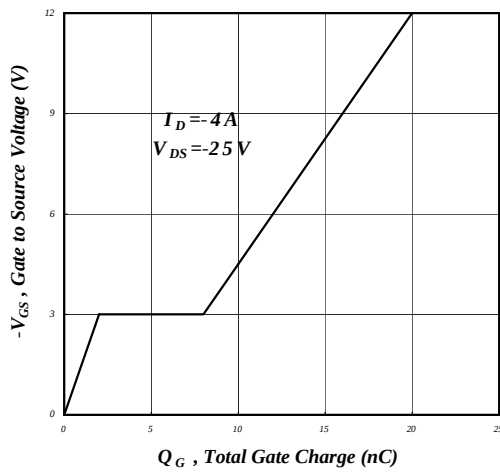


Fig 7. Gate Charge Characteristics

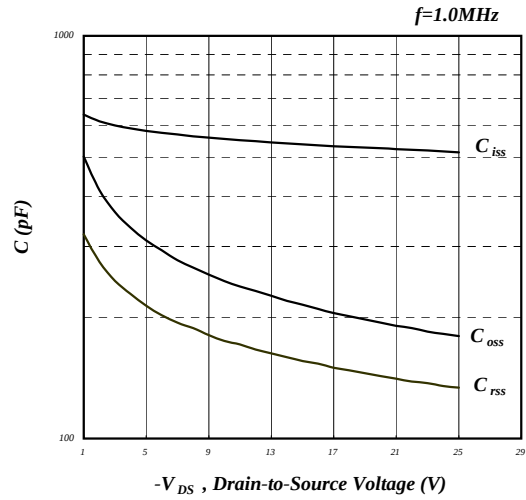


Fig 8. Typical Capacitance Characteristics

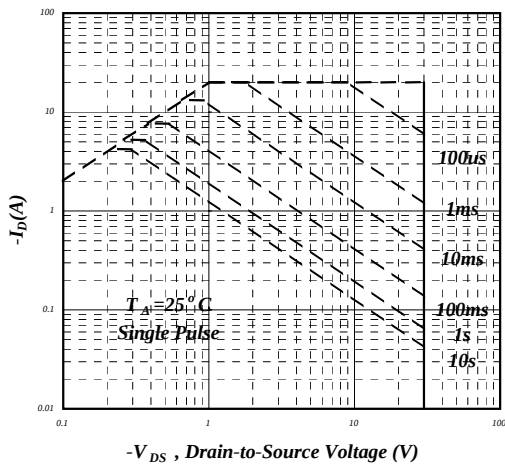


Fig 9. Maximum Safe Operating Area

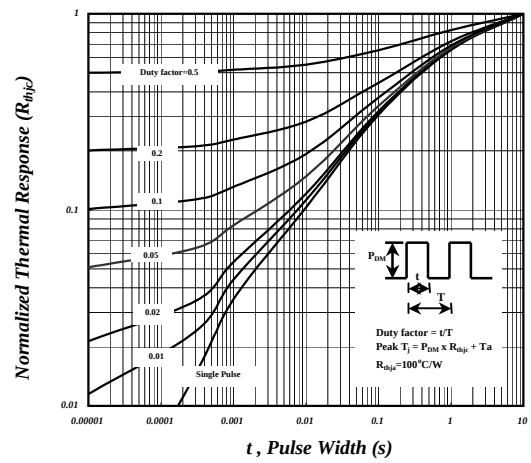


Fig 10. Effective Transient Thermal Impedance

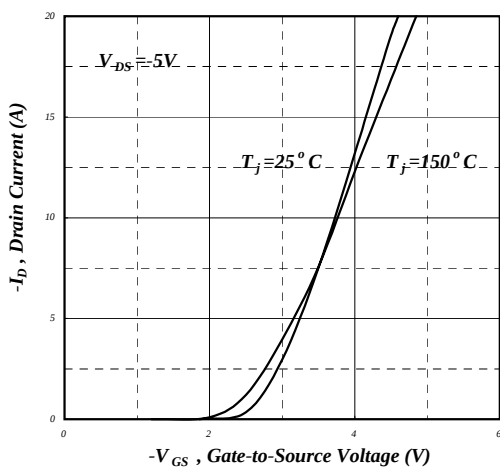


Fig 11. Transfer Characteristics

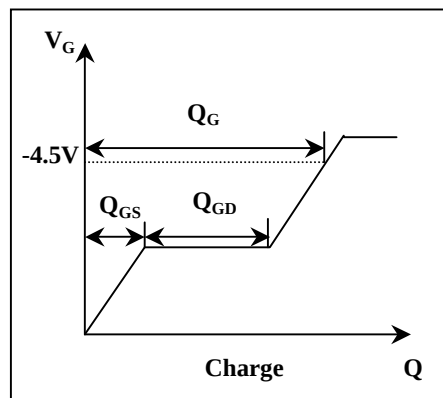


Fig 12. Gate Charge Waveform